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U.S. UTILITY Patent Application

**PATENT NUMBER and
ISSUE DATE**

APPL NUM 10002031	FILING DATE 11/30/2001	CLASS 438	SUBCLASS	GAU 2812	EXAMINER
*APPLICANTS: Yeo Yee-Chia; Chieh Lin Chun; Yang Fu-Liang; Hu Chen Ming;					
**CONTINUING DATA VERIFIED:					
**FOREIGN APPLICATIONS VERIFIED:					
PG-PUB <input checked="" type="checkbox"/> DO NOT PUBLISH <input checked="" type="checkbox"/>		RESCIND <input type="checkbox"/>			
Foreign priority claimed <input type="checkbox"/> yes <input checked="" type="checkbox"/> no		US USC 119 conditions met <input type="checkbox"/> yes <input checked="" type="checkbox"/> no		ATTORNEY DOCKET NO	
Verified and Acknowledged Examiners's initials		TS01-1132			
TITLE : Complementary metal oxide semiconductor transistor technology using selective epitaxy of a strained silicon germanium layer					

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G
ISSUE FEE		DRAWING	
Amount Due	Date Paid	Sheets Drwg.	Figs.Drwg. Print Fig.
<input type="checkbox"/> TERMINAL DISCLAIMER		Primary Examiner	
		Application Examiner	
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